Ksurf. 0 = 1e-6 Ksurf. E = 0; vacan silicon/gas Ksurf. 0 = 1e-6 Ksurf. E = 0.

We have set the value of the recombination constant, not applicable to FINDPRO, Eq. [15]: inter silicon Kr. 0 = 1e-12 Kr. E = 0; vacan silicon Kr. 0 = 1e-12 Kr. E = 0. In fitting the data for Fig. 1, the only fitting parameters have been K_I, γ_P, D_P^i and the electrically active portion of the total P which we have taken to saturate at 2.5×10^{20} cm^{-3}. We set the solubility of P in SUPREM-IV above this

phos ss. temp = 874 ss. conc = 1e21

We set the transfer coefficient for P from the gas to Si at a high value

phos silicon/gas Trn. 0 = 1e3 Trn. E = 0

Finally, we eliminated the traps from SUPREM-IV

trap silicon total = 0 frac. 0 = 0

In both programs the 1-D mesh was set to extend at least to 60 microns, a point at which, for these parameters, I did not increase from its initial equilibrium value I_0.

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ERRATA

In the paper "Theory of Steady-State Passive Films," by Digby D. Macdonald and Mirna Urquidi-Macdonald [*This Journal*, **137,** 2395-2402 (1990)], Eq. [12] and Eq. [13] should be

$$\frac{\partial C_O}{\partial t} = D_O\left(\frac{\partial^2 C_O}{\partial x^2}\right) + 2KD_O\left(\frac{\partial C_O}{\partial x}\right) \qquad [12]$$

$$\frac{\partial C_M}{\partial t} = D_M\left(\frac{\partial^2 C_M}{\partial x^2}\right) - \chi KD_M\left(\frac{\partial C_M}{\partial x}\right) \qquad [13]$$

where $K = \epsilon\gamma$, $\gamma = F/RT$, and ϵ is the electric field strength, $d\phi/dx$. In the original version, ϵ was defined as $-d\phi/dx$ and the signs before the last terms in Eq. [12] and [13] are opposite to those printed above. However, all subsequent equations are correct and the findings of the work are unchanged.

In the paper "Transport Phenomena in Tungsten LPCVD in a Single-Wafer Reactor," by C. R. Kleijn, C. J. Hoogendoorn, A. Hasper, J. Holleman, and J. Middelhoek [*This Journal*, **138,** 509-517 (1991)] the following corrections should be made:

In the 5th and 6th lines of the Abstract and in the 8th line of the right column on page 513 "with the WF_6 inlet pressure" should read "with decreasing WF_6 inlet pressure."

In the left column of page 510, the reference in the 22nd line from the bottom should be (41).

In Eq. [4], $(\nabla \mathbf{v})^T$ should be $(\nabla \mathbf{v})^T$.

In Eq. [9c], [11c], [12c], and [16], $\mathbf{j}_i^c$ should be $\mathbf{j}_i^C$.

In Eq. [11c], j_i^T should be $\mathbf{j}_i^T$.

In Eq. [14] and in The List of Symbols, unit E_A should be kJ · mol^{-1}.

In the caption for Fig. 4, "mole predictions" should be "model predictions."

In the List of Symbols, the unit **g** should be in m · s^{-2}; **I** should be $\underline{\underline{I}}$, $\mathbf{v}_{in}$ should be v_{in}, and superscript c should be C.

In Ref. (1, 4, 15, 17, 43), B. Blewer should be R. S. Blewer.

In the paper "Modeling Calculations of an Aluminium-Air Cell" by Kwong-Yu Chan and Robert F. Savinell [*This Journal*, **138,** pp. 1976-1984 (1991)] in Table I, column 1, $\delta_m = 1$ should be $\lambda_m = 1$; in column 2, $\delta_p = 1$ should be $\lambda_p = 1$ and E_p^{eq} should be $E_p^{eq} = -0.9058$ V; and in column 3 i_c in A/cm^2, η_c in volts. Equations [18] and [19] should be

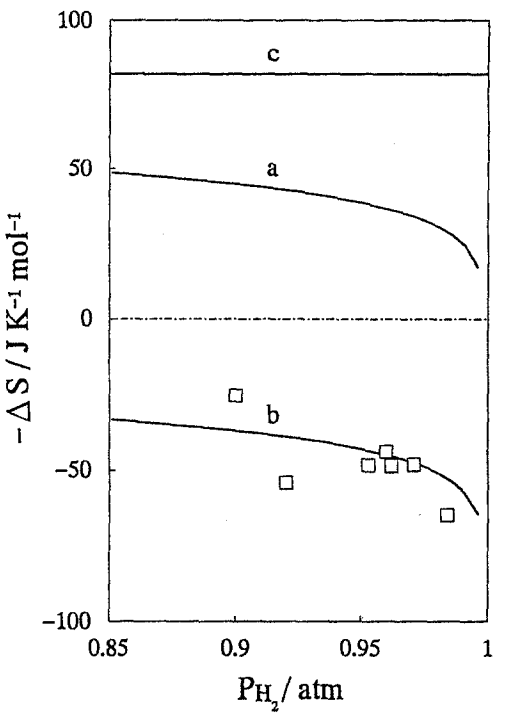
$$\frac{C^{SA}_{OH^-}}{C^*_{OH^-}} = \left[\frac{1 + \dfrac{f(\phi_a - \phi_c)}{2S}\delta_{OH^-}}{1 - \dfrac{f(\phi_a - \phi_c)}{2S}\delta_{OH^-}}\right] - \frac{\dfrac{i_p}{F} + \dfrac{4i_m}{3F}}{\dfrac{D_{OH^-}C^*_{OH^-}}{\delta_{OH^-}}\left[1 - \dfrac{f(\phi_a - \phi_c)}{2S}\delta_{OH^-}\right]} \qquad [18]$$

$$\frac{C^{SA}_{Al(OH)_4^-}}{C^*_{Al(OH)_4^-}} = \left[\frac{1 + \dfrac{f(\phi_a - \phi_c)}{2S}\delta_{Al(OH)_4^-}}{1 - \dfrac{f(\phi_a - \phi_c)}{2S}\delta_{Al(OH)_4^-}}\right] + \frac{\dfrac{1}{3}\dfrac{i_m}{F}}{\dfrac{D_{Al(OH)_4^-}C^*_{Al(OH)_4^-}}{\delta_{Al(OH)_4^-}}\left[1 - \dfrac{f(\phi_a - \phi_c)}{2S}\delta_{Al(OH)_4^-}\right]} \qquad [19]$$

On page 1979 in the first paragraph of the section in Solution Algorithm, $E_c = E_a + V_{cell}$. On page 1980, Case C should read $|i_a| < |i_{cell}| < |i_c|$ and Case D should read $|i_a| > |i_{cell}| > |i_c|$. In Table V in the first column, $E_m^{eq} = -2.4403$ V. In the Acknowledgments, Eltech is in Chardon, Ohio.

In the article "Thermal Desorption and Infrared Studies at Sol-Gel Derived SiO_2 Coatings on Si Wafers" by Rolf Sokoll, Hans-Jürgen Tiller, and Thomas Hoyer [*This Journal*, **138,** 2150-2153 (1991)] the acronym TPD for temperature-programmed desorption should have capitalized. On page 2150 in the second column, the second line should read "(v/o) TMOS and 20-40 v/o . . ." and line 28 should read "$4 \cdot 10^{-5}$ Pa; 4 h) . . ." On page 2151 in Table I, footnote b should apply to "Assignment" and footnote a should be in that column following ν_{as} (Si-O-Si). On page 2152, the temperatures in line 15 should be 720 and 710 K. In the right column on page 2152, the sentence beginning on line 17 should read "Between *ca.* 700 and 800 K the CH_3 groups are removed from the film and a pure SiO_2 layer results (Fig. 8, curve 4) as shown with sol-gel systems M and V, respectively." L. C. Bellamy is the author of Ref. (4).

In the article entitled "Dependence of Entropy Change of Single Electrodes on Partial Pressure in Solid Oxide Fuel Cells" by Kiyoshi Kanamura, Shoji Yoshioka, and Zen-ichiro Takehara [*This Journal*, **138,** 2165-2167 (1991)], Fig. 3 on page 2167 should be



In the article "Experimental Approach to the Impedance Spectroscopy Technique" by G. Chiodelli and P. Lupotto [*This Journal*, **138,** 2703-2711 (1991)], the following corrections should be noted. In the fourth line of the Abstract should have inserted "of" in "two orders of magnitude of impedance . . .". On page 2704, in the left column, five lines down $Z' = \mathrm{Re}\ Z = Z_o \cos(\omega)$. On the same page in the right column, four lines from the bottom, $M(\omega) = j\omega Z(\omega)$. On page 2710 in the first paragraph in the left column in the next to last line "with a 100 mΩ resistor" should be "with a 100 MΩ resistor." The Italian CNR-ENEA assisted in meeting the publication costs of this article.

In this article "AC Impedance of Faradaic Reactions Involving Electrosorbed Intermediates: Examination of Conditions Leading to Pseudoinductive Behavior Represented in Three-Dimensional Impedance Spectroscopy Diagrams" by Lijun Bai and B. E. Conway [*This Journal*, **138,** 2897-2907 (1991)] it should be noted that Lijun Bai is an Active Member of The Electrochemical Society. On page 2898 Eq. [9] should read $B = (F^2/q_i)\,[(\partial v_i/\partial\theta)_E + (\partial v_2/\partial\theta)_E]$, etc. On page 2904, left column, line 10 it should read "3 d phase plot, as $E \leq 0.01$ V." On page 2906, Eq. [A-4] should read

$$(q_i/F)\,\delta\left(\frac{d\theta}{dt}\right) = \left(\frac{\partial r_i}{\partial E}\right)_{\theta 1 \ldots \theta n} \delta E + \sum_{k=1}^{n}\left(\frac{\partial r_i}{\partial \theta_k}\right)_{\theta LE} \delta\theta_k \quad [A\text{-}4]$$

In the article "Corrosion Rate Measurement under Cathodic Polarization by Faradaic Rectification" by Rengaswamy Srinivasan and John C. Murphy [*This Journal*, **138,** 2960-2964 (1991)], the correct form of Eq. [12] was used in the calculations and therefore the results in the paper are correct. But the correct statements following Eq. [11] and the correct form of Eq. [12] should be

Substitution for $i_{0,M}$ in Eq. [11] from Eq. [10] gives the expression for corrosion current as

$$i_{cor} = \frac{i_{fr} + i_{cp} - i_{cp}\{\exp[\delta_c f(\eta_2 - \eta_1)\}}{I_0(\alpha_c')\{A'\} - I_0(\beta_a')\{B'\}} \quad [12]$$

where $\eta_1 = E_1 - E_{cor}$; $\eta_2 = E_2 - E_{cor}$; $A' = \exp[-\alpha_c f\eta_1] - \exp[\delta_c f\eta_2 - \delta_c f\eta_1 - \alpha_c f\eta_2]$; and $B' = \exp[\beta_a f\eta_1] - \exp[\delta_c f\eta_2 - \delta_c f\eta_1 + \beta_a f\eta_2]$.

In the Table of Contents for the November 1991 issue of the *Journal* [*This Journal*, **138,** 516C (1991)], the authors of the Letter entitled "Dissolution Rate of III-V Compound Oxides. Influence of Cerium Species" on page L65, should be E. M. Khoumri, A. Etchberry, O. Poliakoff, C. Debiemme-Chouvy, and J. L. Sculfort.